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# The Influence of Mechanical Stress on Electrooptical Coefficients $r_{22}$ and $n_e^3 r_{33} - n_0^3 r_{13}$ in LiNbO<sub>3</sub> and LiTaO<sub>3</sub> Crystals

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## Abstract

The combined piezo-electrooptical effect in LiNbO<sub>3</sub> and LiTaO<sub>3</sub> crystals is studied. It is shown that the mechanical stresses change notably the electrooptical (EO) coefficient  $r_{22}$  of lithium niobate and the coefficient  $n_e^3 r_{33} - n_0^3 r_{13}$  of lithium tantalate crystals. The largest increment of electrooptical coefficients under the mechanical stresses is observed in LiNbO<sub>3</sub> crystals at the experimental geometry of  $k||Z$ ,  $E||Y$  and  $\sigma||Y$ . In case of LiNbO<sub>3</sub> crystals subjected to the compressing mechanical stress  $\sigma_2 = 2.0 \times 10^7 \text{ N/m}^2$ , the EO coefficient  $r_{22}$  increases approximately two times, while the half-wave voltage decreases by the same value. The obtained dependence of the angle  $\xi_3$  of optical indicatrix rotation under the applied electric field  $E_l$  and the mechanical compressive stress  $\sigma_l$  testifies a possibility for controlling the optical indicatrix orientation in LiNbO<sub>3</sub> crystals in the range of  $|0-45|$  deg.

**Key words:** piezo-electrooptical effect, LiNbO<sub>3</sub>, LiTaO<sub>3</sub>

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## Introduction

LiNbO<sub>3</sub> and LiTaO<sub>3</sub> crystals are well known as efficient electrooptical (EO) materials. They are widely used in different EO devices. The EO properties of LiNbO<sub>3</sub> and LiTaO<sub>3</sub> crystals are already well studied [1,2]. On the other hand, lithium niobate and lithium tantalate crystals are rather sensitive to different external influences, e.g., temperature, optical radiation and the mechanical stresses. Concerning the influence of mechanical stresses on the optical properties of the mentioned crystals, their piezo-optical coefficients have a large magnitude [1,3]. It has been shown in our recent works that the EO coefficients could be changed by application of mechanical stress due to a combined piezo-electrooptical effect [4-6]. It should mean a possibility to operate the performance characteristic of EO device, using the change of its EO coefficients induced by external mechanical stresses. Finally, we notice that the

EO coefficients dealt with in the EO devices based on LiNbO<sub>3</sub> and LiTaO<sub>3</sub> crystals, are  $r_{22}$  and  $n_0^3 r_{13} - n_e^3 r_{33}$ , respectively.

The present paper is devoted to studies of the changes in the mentioned EO coefficients due to the applied mechanical stresses.

## Experimental

All the studies were carried out with the known Senarmont technique. He-Ne laser with the wavelength of radiation 632.8 nm was used as a light source. The geometry of the experiments was  $k||Y$ ,  $E||Z$ ,  $\sigma||X$ ,  $\sigma||Z$  for LiTaO<sub>3</sub> crystals and  $k||Z$ ,  $E||Y$ ,  $\sigma||Y$  for LiNbO<sub>3</sub> crystals.

The change of the birefringence  $\delta(\Delta n)_{12}$  under the mutual application of the electric field  $E_2$  and the mechanical stress  $\sigma_2$  to LiNbO<sub>3</sub> crystals can be written as

$$\delta(\Delta n)_{12} = 1/2 n_0^3 r_{22} E_2 + 1/2 n_0^3 (\pi_{12} - \pi_{22}) \sigma_2 + 1/2 n_0^3 N_{222} E_2 \sigma_2, \quad (1)$$

while the corresponding change of the EO coefficient  $r_{22}$  caused by the mechanical stress is given by

$$r_{22} = N_{222} \sigma_2, \quad (2)$$

where  $\pi_{ij}$  are the components of piezooptical tensor and  $N_{ijk}$  the components of the piezo-electrooptical fifth-rank polar tensor. For LiTaO<sub>3</sub> crystals, the change of the birefringence  $\delta(\Delta n)_{13}$  under the mutual application of the electric field  $E_3$  and the mechanical stresses  $\sigma_3$  and  $\sigma_1$  can be written as

$$\begin{aligned} \delta(\Delta n)_{13} = & 1/2(n_3^3 r_{33} - n_1^3 r_{13})E_3 + \\ & + 1/2(n_3^3 \pi_{33} - n_1^3 \pi_{13})\sigma_3 + \\ & + 1/2(n_3^3 N_{333} - n_1^3 N_{133})E_3 \sigma_3 \end{aligned}, \quad (3)$$

$$\begin{aligned} \delta(\Delta n)_{13} = & 1/2(n_3^3 r_{33} - n_1^3 r_{13})E_3 + \\ & + 1/2(n_1^3 \pi_{11} - n_3^3 \pi_{31})\sigma_1 + \\ & + 1/2(n_1^3 N_{131} - n_3^3 N_{331})E_3 \sigma_1 \end{aligned}, \quad (4)$$

respectively, whereas the change of the EO coefficients  $n_3^3 r_{33} - n_1^3 r_{13}$  under the mechanical stress is as follows:

$$(n_3^3 r_{33} - n_1^3 r_{13}) = (n_1^3 N_{333} - n_3^3 N_{133}), \quad (5)$$

$$(n_3^3 r_{33} - n_1^3 r_{13}) = (n_1^3 N_{131} - n_3^3 N_{331}). \quad (6)$$

As a consequence, one can assume that the application of mechanical strains to the LiNbO<sub>3</sub>

and LiTaO<sub>3</sub> crystals would lead to changes in both the EO coefficients and the half-wave electric voltage.

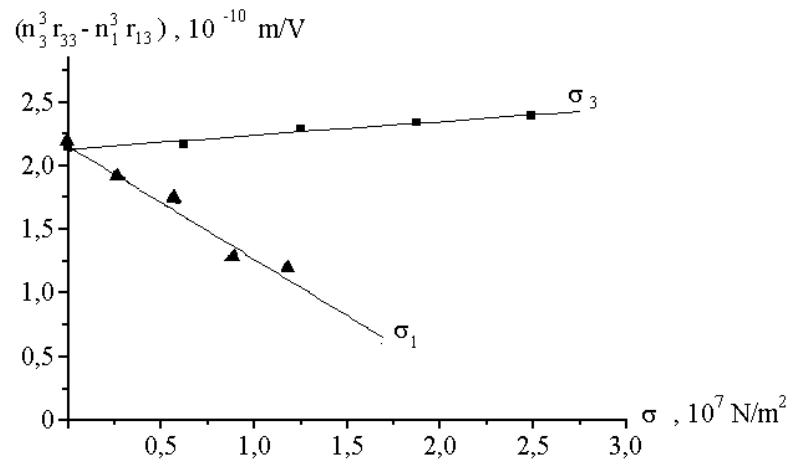
## Results and discussion

The change of the EO coefficient  $n_3^3 r_{33} - n_1^3 r_{13}$  in LiTaO<sub>3</sub> crystals observed under the applied mechanical stress is presented in Fig.1.

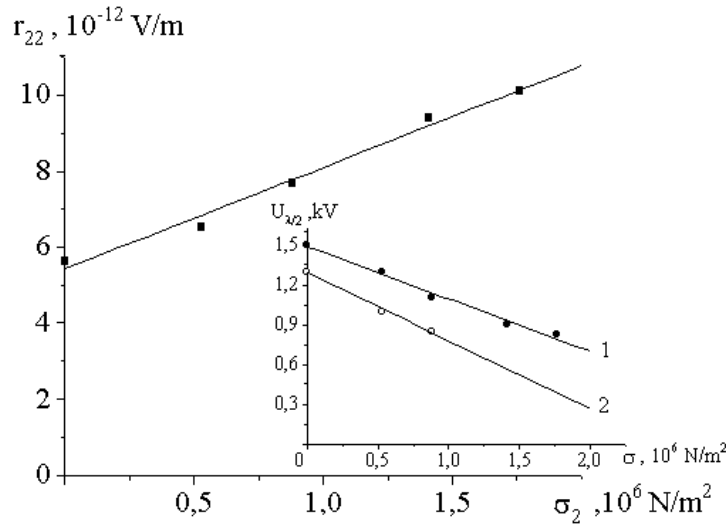
As seen from Fig. 1, the influence of mechanical stress  $\sigma_3$  on LiTaO<sub>3</sub> crystals does not lead to essential changes in the EO coefficient, while the influence of compressing mechanical stress  $\sigma_1$  on LiTaO<sub>3</sub> crystals causes decreasing the EO coefficient  $n_3^3 r_{33} - n_1^3 r_{13}$ . However, in case of the compressive mechanical stress  $\sigma_3 = 2.0 \times 10^7 \text{ N/m}^2$  applied to LiNbO<sub>3</sub> crystals, the EO coefficient  $r_{22}$  increases approximately two times (Fig. 2). That is why one of the most important functional characteristics of EO devices based on the LiNbO<sub>3</sub> crystals, the half-wave voltage,

$$U_{\lambda/2} = \frac{\lambda}{n_0^3 r_{22}} \frac{d_y}{d_z}, \quad (7)$$

(with  $\lambda$  being the light wavelength,  $d_y$  the sample thickness along the direction of electric field, and  $d_z$  the sample thickness along the light propagation) can be decreased through application of mechanical stresses. Since the



**Fig. 1.** The dependence of EO coefficient  $n_3^3 r_{33} - n_1^3 r_{13}$  on the mechanical stresses  $\sigma_1$  and  $\sigma_3$  for LiTaO<sub>3</sub> crystals ( $\lambda = 632.8 \text{ nm}$ ,  $T = 20^\circ \text{C}$ ).



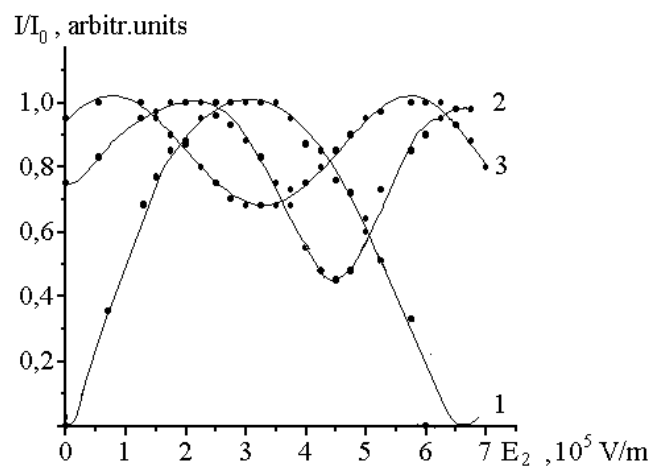
**Fig. 2.** The dependence of EO coefficient  $r_{22}$  on the mechanical stress  $\sigma_2$  for LiNbO<sub>3</sub> crystals ( $\lambda=632.8\text{nm}$ ,  $T=20^\circ\text{C}$ ); insert: the dependence of the half-wave voltage for LiNbO<sub>3</sub> crystals subjected to the mechanical stress  $\sigma_2$ : 1 – the data calculated on the basis of measurements of EO coefficient, 2 – those experimentally obtained on the basis of direct measurements of the half-wave voltage (see Fig.3).

dimensions of LiNbO<sub>3</sub> crystal sample in our case were  $d_y=4\times 10^{-3}\text{m}$  and  $d_z=25\times 10^{-3}\text{m}$ , one can easily calculate the corresponding change in the half-wave voltage due to the mechanical stress (see Fig. 2, insert).

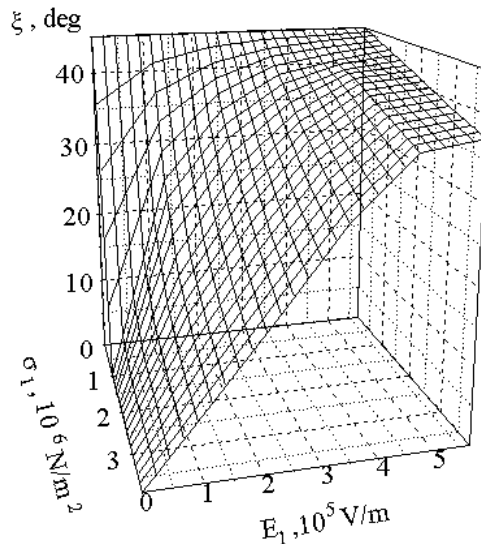
The experimental dependences of the light transmission on the electric field obtained for the LiNbO<sub>3</sub> crystal placed in the diagonal position between the crossed polarizers is presented in Fig.3. One can see that the half-

wave voltage decreases when the compressive stress  $\sigma_2$  is applied to LiNbO<sub>3</sub> crystals. At the same time, the modulation depth also decreases, due to the piezooptical effect.

The application of the electric field  $E||X$  and the mechanical stress  $\sigma||X$  to LiNbO<sub>3</sub> crystals should induce the rotation of the optical indicatrix by the angle depending on the values of both the electric field and the mechanical stress, according to the relation



**Fig. 3** The dependences of the light transmission on the electric field for LiNbO<sub>3</sub> crystals placed in the diagonal position between the crossed polarizers at different values of the mechanical stress: 1- $\sigma_2=0\text{ N/m}^2$ , 2- $\sigma_2=5.3\times 10^5\text{ N/m}^2$  and 3- $\sigma_2=8.8\times 10^5\text{ N/m}^2$  ( $\lambda=632.8\text{nm}$ ,  $T=20^\circ\text{C}$ )



**Fig.4.** The dependence of the angle of optical indicatrix rotation in LiNbO<sub>3</sub> crystals under the mutual influence of the electric field  $E_1$  and the mechanical stress  $\sigma_1$  ( $\lambda=632.8\text{nm}$ ,  $T=20^\circ\text{C}$ ).

$$\tan 2\xi = \frac{2r_{22}E_1}{(\pi_{11} - \pi_{12})\sigma_1}, \quad (8).$$

This dependence is presented in Fig. 4.

The data of Fig. 4 clearly demonstrate that a mutual influence of the electric field and the mechanical stress enables one to control the orientation of optical indicatrix in LiNbO<sub>3</sub> crystals.

## Conclusions

The combined piezo-electrooptical effect in the LiNbO<sub>3</sub> and LiTaO<sub>3</sub> crystals is studied in this work. It is shown that the mechanical stresses change the EO coefficients  $r_{22}$  of lithium niobate and the coefficient  $n_3^3r_{33} - n_1^3r_{13}$  of lithium tantalate crystals. The largest increment of EO coefficients under the application of mechanical stress was observed in LiNbO<sub>3</sub> crystals at the following experimental geometry:  $k||Z, E||Y$  and  $\sigma||Y$ . It is revealed that the EO coefficient  $r_{22}$  of LiNbO<sub>3</sub> crystals increase, while the half-wave voltage decreases approximately two times, when the compressive mechanical stress  $\sigma_2=2.0 \times 10^7 \text{N/m}^2$  is applied. The obtained dependence of the angle  $\xi_3$  of optical indicatrix

rotation due to the applied electric field  $E_1$  and the mechanical compressive stress  $\sigma_1$  testifies that it is possible to operate the optical indicatrix orientation in LiNbO<sub>3</sub> crystals in the range as large as  $|0-45|$  deg.

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